

MBRB10100CT

Rev.F May.-2016

/ Descriptions

TO-263

Schottky Diode in a TO-263 Plastic Package.

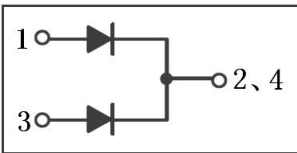
/ Features

Low power loss, high efficiency.

/ Applications

For use in low voltage,high frequency inverters, free wheeling, and polarity protection applications.

/ Equivalent Circuit



/ Pinning



PIN1 Anode

PIN 2 4 Cathode

PIN 3 Anode

/ h_{FE} Classifications & Marking

See Marking Instructions.

/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Reverse Voltage	V_{RRM} V_{RWM} V_{RM}	100	V
RMS Reverse Voltage	$V_{R(RMS)}$	70	V
Average forward rectified Current	I_F	2X5	A
Non Repetitive Peak Surge Current	I_{FSM}	125	A
Thermal Resistance Junction to Case	R_{Jc}	2.5	/W
Junction Temperature Range	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

/ Electrical Characteristics(Ta=25)

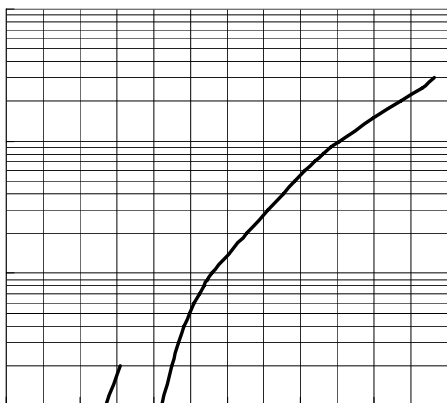
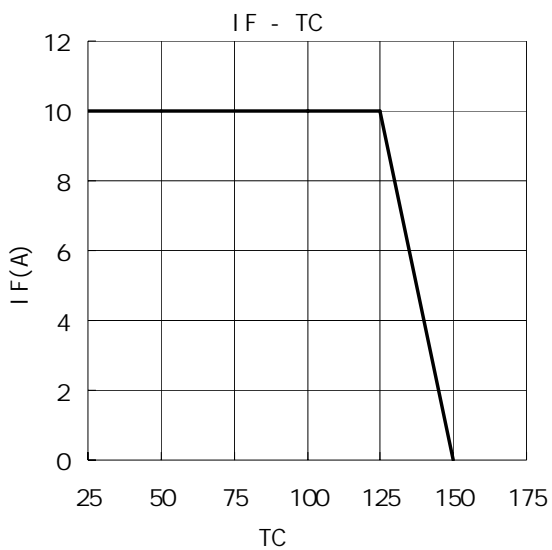
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse Voltage	V_R	$I_R=0.3mA$	100			V
Forward Voltage	V_{FM}	$I_F=5.0A$ $T_j=25$			0.85	V
		$I_F=5.0A$ $T_j=125$			0.75	V
		$I_F=10A$ $T_j=25$			0.95	V
		$I_F=10A$ $T_j=125$			0.85	V
Instantaneous Reverse Current	I_R Note 1	$V_R=100V$ $T_j=25$			10	uA
		$V_R=70V$ $T_j=125$			1	mA
		$V_R=100V$ $T_j=125$			5	mA

/Notes

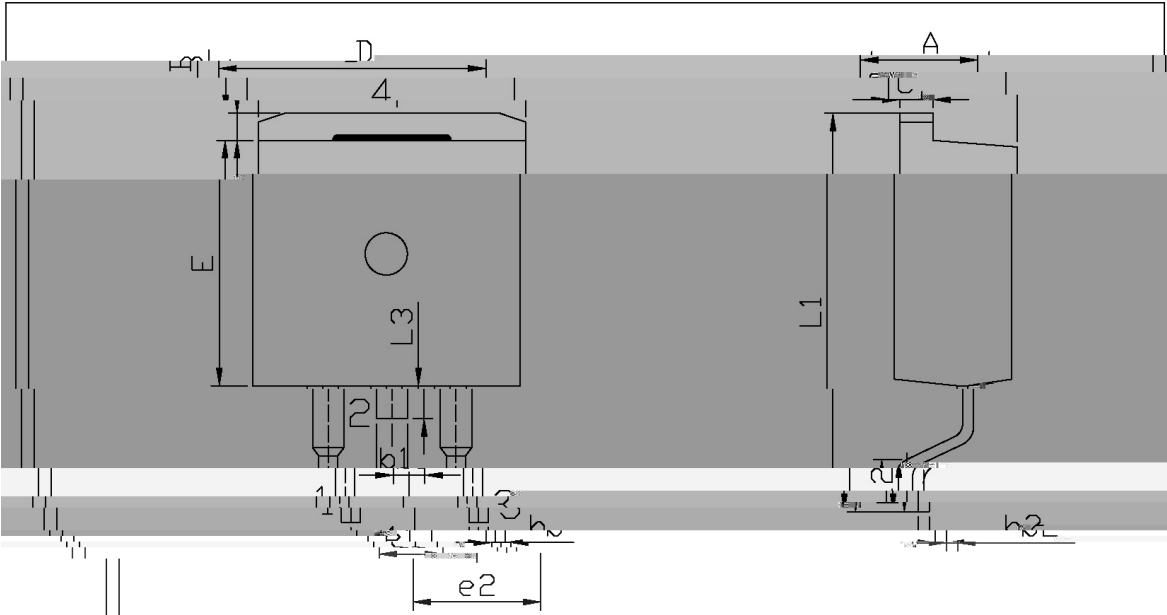
1. /Short duration pulse test used to minimize self-heating effect.
2. / Unless otherwise noted, values for the parameters of a single chip



/ Electrical Characteristic Curve



/ Package Dimensions



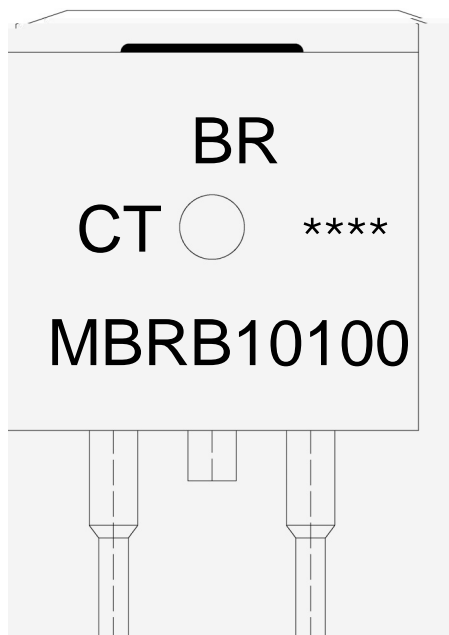
单位: mm

Dimensions	Symbol	Dimensions In Millimeters	Symbol	Dimensions In Millimeters
Max		Min	Max	Min
9.40	A	4.30	L ₁	9.00
2.71	B	1.00	e ₁	2.34

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/ Marking Instructions



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MBRB10100

CT:

Note:

BR: Company Code

MBRB10100 Product Type.

CT: Internal Structure

****: Lot No. Code, code change with Lot No.

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